THERMAL DATA

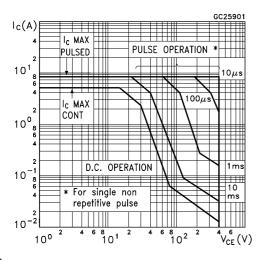
R _{thj-case}	Thermal Resistance Junction-Ca	ise Max	1.78	°C/W
R _{thj-amb}	Thermal Resistance Junction-An	nbient Max	62.5	°C/W

ELECTRICAL CHARACTERISTICS ($T_{case} = 25$ $^{\circ}C$ unless otherwise specified)

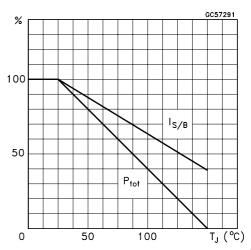
Symbol Parameter		Test Conditions	Min.	Тур.	Max.	Unit
I _{CES}	Collector Cut-off Current (V _{BE} = 0)	V _{CE} = 800 V V _{CE} = 800 V T _j = 125 °C			100 500	μΑ μΑ
I _{CEO}	CEO Collector Cut-off VCE = 400 V Current (I _B = 0)				250	μΑ
$V_{\text{CEO(sus)}^{*}}$	Collector-Emitter Sustaining Voltage (I _B = 0)	I _C = 100 mA L = 25 mH	400			V
V _{EBO}	Emitter-Base Voltage (I _C = 0)	I _E = 10 mA	9			V
V _{CE(sat)} *	Collector-Emitter Saturation Voltage	$I_C = 1 \text{ A}$ $I_B = 0.2 \text{ A}$ $I_C = 2 \text{ A}$ $I_B = 0.4 \text{ A}$ $I_C = 3 \text{ A}$ $I_B = 0.75 \text{ A}$			0.5 0.7 1.1	V V V
V _{BE(sat)} *	Base-Emitter Saturation Voltage	$I_C = 1 \text{ A}$ $I_B = 0.2 \text{ A}$ $I_C = 2 \text{ A}$ $I_B = 0.4 \text{ A}$			1.1 1.2	V V
h _{FE} *	DC Current Gain	$I_C = 2 A$ $V_{CE} = 5 V$ $I_C = 10 \text{ mA}$ $V_{CE} = 5 V$	8 10			
t _s t _f	RESISTIVE LOAD Storage Time Fall Time	$I_{C} = 2 \text{ A}$ $V_{CC} = 250 \text{ V}$ $t_{p} = 30 \mu \text{s}$ $I_{B1} = -I_{B2} = 0.4 \text{ A}$	1.5		2.5 0.8	μs μs
t _s t _f	INDUCTIVE LOAD Storage Time Fall Time	$\begin{split} I_{C} &= 2 \; A & I_{B1} &= 0.4 \; A \\ V_{BE(off)} &= -5 \; V & R_{BB} &= 0 \; \Omega \\ V_{CL} &= 250 \; V & L &= 200 \; \mu H \\ T_{j} &= 125 \; ^{\circ}C \end{split}$		1.3 100		μs ns
Vf	Diode Forward Voltage	I _C = 2 A			2.5	V

^{*} Pulsed: Pulse duration = 300 μs, duty cycle 1.5 %

Safe Operating Area



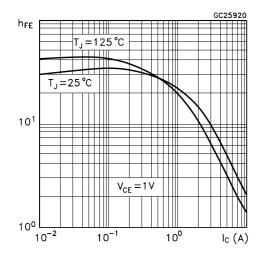
Derating Curve



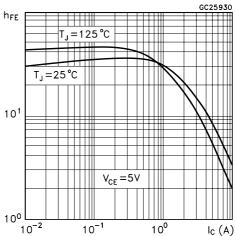
4

2/6

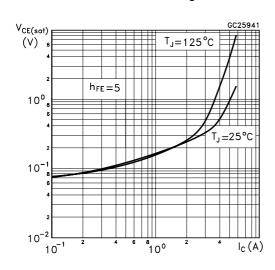
DC Current Gain



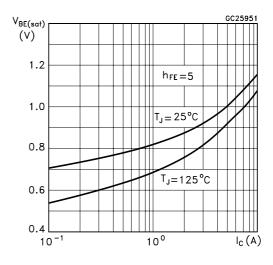
DC Current Gain



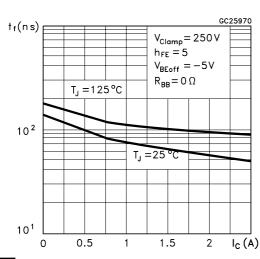
Collector Emitter Saturation Voltage



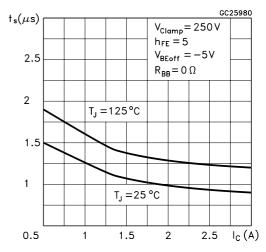
Base Emitter Saturation Voltage



Inductive Fall Time

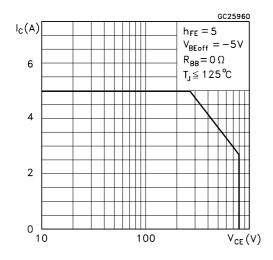


Inductive Storage Time

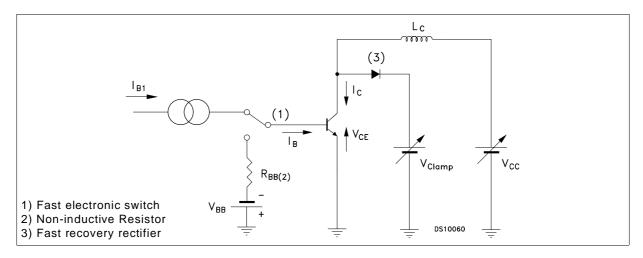


477

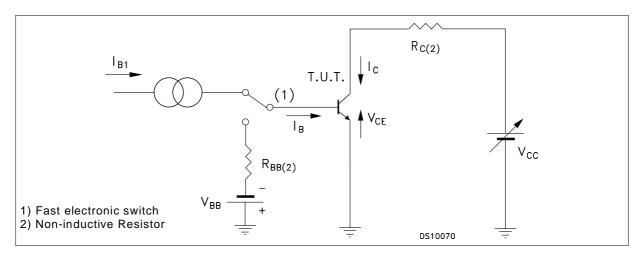
Reverse Biased SOA



Inductive Load Switching Test Circuit



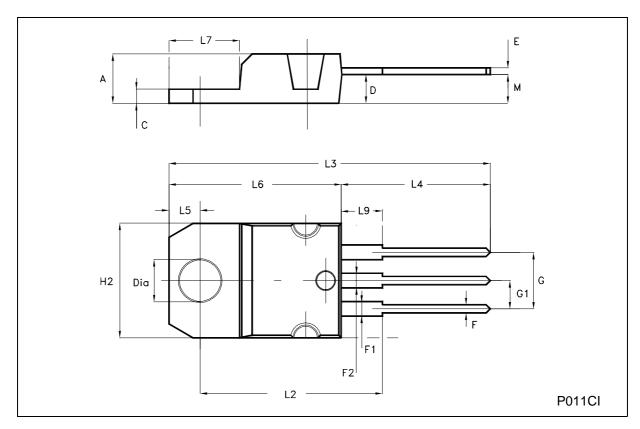
Resistive Load Switching Test Ciurcuit



4/6

TO-220 MECHANICAL DATA

DIM	mm		inch			
DIM.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
Α	4.40		4.60	0.173		0.181
С	1.23		1.32	0.048		0.052
D	2.40		2.72	0.094		0.107
E	0.49		0.70	0.019		0.027
F	0.61		0.88	0.024		0.034
F1	1.14		1.70	0.044		0.067
F2	1.14		1.70	0.044		0.067
G	4.95		5.15	0.194		0.202
G1	2.40		2.70	0.094		0.106
H2	10.00		10.40	0.394		0.409
L2		16.40			0.645	
L4	13.00		14.00	0.511		0.551
L5	2.65		2.95	0.104		0.116
L6	15.25		15.75	0.600		0.620
L7	6.20		6.60	0.244		0.260
L9	3.50		3.93	0.137		0.154
М		2.60			0.102	
DIA.	3.75		3.85	0.147		0.151



Information furnished is believed to be accurate and reliable. However, STMicroelectronics assumes no responsibility for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of STMicroelectronics. Specification mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information previously supplied. STMicroelectronics products are not authorized for use as critical components in life support devices or systems without express written approval of STMicroelectronics.

The ST logo is a trademark of STMicroelectronics

© 2003 STMicroelectronics – Printed in Italy – All Rights Reserved STMicroelectronics GROUP OF COMPANIES

Australia - Brazil - Canada - China - Finland - France - Germany - Hong Kong - India - Israel - Italy - Japan - Malaysia - Malta - Morocco - Singapore - Spain - Sweden - Switzerland - United Kingdom - United States.

http://www.st.com

47/

Mouser Electronics

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

STMicroelectronics: BUL381D